

FEATURES

- \varnothing 800 μm active area
- Blue enhanced
- High QE at blue range
- Fast rise time

DESCRIPTION

0.50 mm² High Speed, High Gain, Blue Enhanced Avalanche Photodiode with P on N construction. Hermetically packaged in a case isolated TO-52-S1 with a UV transmitting clear glass window cap.

APPLICATIONS

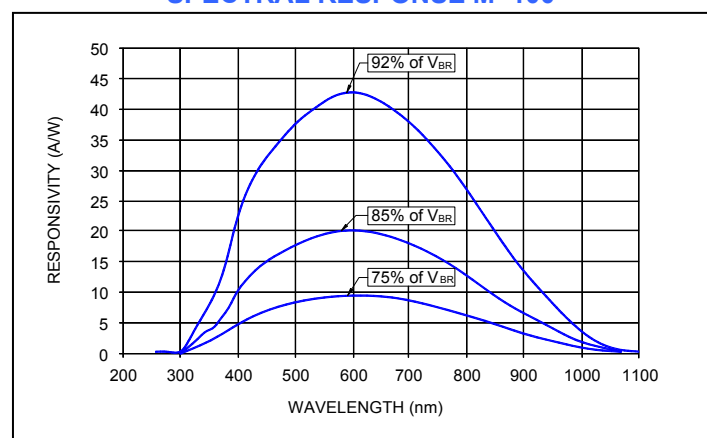
- Analytical equipment
- Scintillation
- Medical equipment
- High speed photometry



ABSOLUTE MAXIMUM RATING

| SYMBOL | PARAMETER | MIN | MAX | UNITS |
|------------------------|--|-----|------|---------------|
| T _{STG} | Storage Temp | -55 | +125 | °C |
| T _{OP} | Operating Temp | -40 | +85 | °C |
| T _{SOLDERING} | Soldering Temp 10 seconds | | +260 | °C |
| | Electrical Power Dissipation @ 22°C | - | 100 | mW |
| | Optical Peak Value, once for 1 second | - | 200 | mW |
| I _{PH} (DC) | Continuous Optical Operation ≤ 1 mA for signal 50 μs "on" / 1 ms "off" | - | 250 | μA |

SPECTRAL RESPONSE M=100

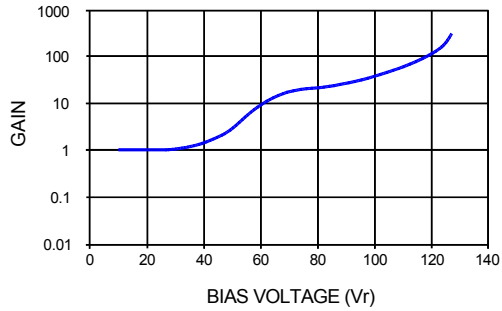


ELECTRO-OPTICAL CHARACTERISTICS @ 23 °C

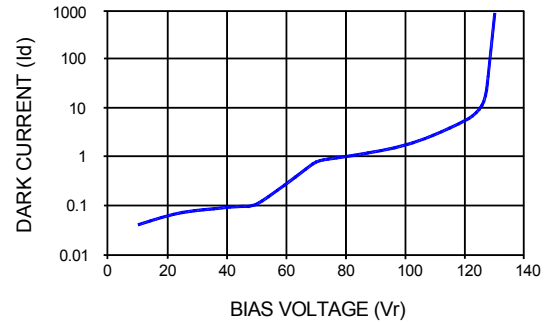
| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|------------------|--|--|-----|-------------------------|-----|----------------------|
| I _D | Dark Current | M = 100 | --- | 1.0 | 5.0 | nA |
| C | Capacitance | M = 100 | --- | 2.5 | --- | pF |
| V _{BR} | Breakdown Voltage | I _D = 2 μA | 100 | 200 | --- | V |
| | Temperature Coefficient of V _{BR} | | --- | 0.88 | --- | V/K |
| | Responsivity | M = 100; λ = 400 nm | --- | 25 | --- | A/W |
| | | M = 100; λ = 500 nm | --- | 35 | --- | |
| | | M = 100; λ = 600 nm | --- | 40 | --- | |
| Δf_{3dB} | Bandwidth | -3dB | --- | 175 | --- | MHz |
| t _r | Rise Time | λ = 410 nm; R _L = 50 Ω | --- | 1 | --- | ns |
| | Optimum Gain | | 50 | --- | 80 | |
| | Noise Current | M = 100 | --- | 0.25 | --- | pA/Hz ^{1/2} |
| | Max Gain | | 200 | 500 | --- | |
| NEP | Noise Equivalent Power | M = 100; λ = 410 nm | --- | 1.0 X 10 ⁻¹⁴ | --- | W/Hz ^{1/2} |

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

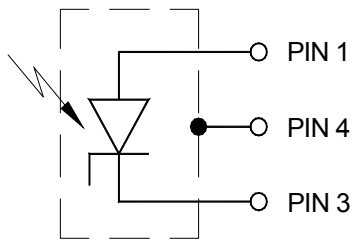
TYPICAL GAIN vs BIAS VOLTAGE



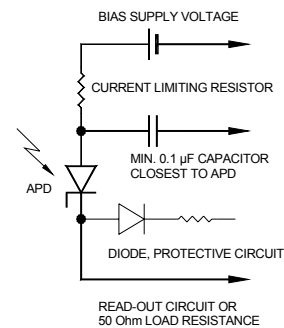
TYPICAL DARK CURRENT vs BIAS VOLTAGE



DEVICE SCHEMATIC



SUGGESTED CIRCUIT SCHEMATIC



APPLICATION NOTES

- Current should be limited by a protecting resistor or current limiting IC inside the power supply.
- Use of low noise read-out IC.
- For high gain applications ($M > 50$) bias voltage should be temperature compensated.
- For low light level applications, blocking of ambient light should be used.

HANDLING PRECAUTIONS:

- Soldering temperature - 260°C for 10 seconds max. The device must be protected against solder flux vapor.
- Minimum pin length - 2 mm
- ESD protection - Standard precautionary measures are sufficient.
- Storage - Store devices in conductive foam.
- Avoid skin contact with window.
- Clean window with Ethyl alcohol if necessary.
- Do not scratch or abrade window.

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